

Serial No.:	10/605,100	Art Unit:	2818
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IN THE ABSTRACT

Please amend the abstract to read as follows:

-- ~~A method is provided for forming an~~ **In an** SOI MOSFET device with a silicon layer formed on a dielectric layer, ~~with a gate electrode stack [[,]]~~ **is formed** with sidewall spacers on sidewalls of the gate electrode stack, ~~and raised~~ **Raised** source/drain regions **are** formed on the surface of the silicon layer. The gate electrode stack comprises a gate electrode formed of polysilicon over a gate dielectric layer formed on the surface of the silicon layer. A plug of dielectric material ~~is formed in~~ **fills** a notch **the edges of** ~~[[in]]~~ a cap layer above the gate polysilicon **and beneath a hard mask layer that overlies the cap layer.** The sidewalls of the gate electrode ~~[[is]]~~ **are** covered by the sidewall spacers which cover a portion of the plug for the purpose of eliminating the exposure of the gate polysilicon, so that formation of spurious epitaxial growth during the formation of raised source/drain regions is avoided. --